

Description

Available in through-hole fullpack package, the T1210T-8FP Triac can be used for the on/off or phase angle control function in general purpose AC switching. This device can be directly driven by a microcontroller thanks to its 10 mA gate current requirement. Provide UL certified insulation rated at 2000 VRMS.

Table 1. Device summary

Symbol	Value	Unit
$I_{T(rms)}$	12	A
V_{DRM}, V_{RRM}	800	V
V_{DSM}, V_{RSM}	900	V
I_{GT}	10	mA

Features

- Three triggering quadrants Triac
- ECOPACK[®]2 compliant component
- Complies with UL insulation safety standards (File ref: E81734)
- High performance Triac:
 - High T_j family
 - High di/dt family
 - High dV/dt family
- Insulated package TO-220FPAB:
 - Insulated voltage: 2000 VRMS

Applications

- General purpose AC line load switching
- Motor control circuits
- Small home appliances
- Lighting control
- Inrush current limiting circuits
- Overvoltage crowbar protection

1 Characteristics

Table 2. Absolute maximum ratings ($T_j = 25\text{ °C}$ unless otherwise stated)

Symbol	Parameter		Value	Unit	
$I_{T(rms)}$	On-state rms current (full sine wave)		$T_c = 99\text{ °C}$	12	A
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_j initial = 25 °C)	F = 50 Hz	t = 20 ms	90	A
		F = 60 Hz	t = 16.7 ms	95	
I^2t	I^2t value for fusing, T_j initial = 25 °C		$t_p = 10\text{ ms}$	54	A ² s
V_{DRM}, V_{RRM}	Repetitive surge peak off-state voltage		$T_j = 150\text{ °C}$	600	V
			$T_j = 125\text{ °C}$	800	
V_{DSM}, V_{RSM}	Non repetitive surge peak off-state voltage		$t_p = 10\text{ ms}$	900	V
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}, t_r \leq 100\text{ ns}$	F = 100 Hz		100	A/ μ s
I_{GM}	Peak gate current	$t_p = 20\text{ }\mu$ s	$T_j = 150\text{ °C}$	4	A
$P_{G(AV)}$	Average gate power dissipation		$T_j = 150\text{ °C}$	1	W
T_{stg} T_j	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 150	°C
T_L	Maximum lead temperature for soldering during 10 s			260	°C
V_{ins}	Insulation rms voltage, 1 minute			2	kV

Table 3. Electrical characteristics ($T_j = 25\text{ °C}$, unless otherwise stated)

Symbol	Test conditions	Quadrant		Value	Unit
$I_{GT}^{(1)}$	$V_D = 12\text{ V}, R_L = 30\text{ }\Omega$	I - II - III	Min.	0.5	mA
			Max.	10	
V_{GT}	$V_D = 12\text{ V}, R_L = 30\text{ }\Omega$	I - II - III	Max.	1.3	V
V_{GD}	$V_D = V_{DRM}, R_L = 3.3\text{ k}\Omega, T_j = 150\text{ °C}$	I - II - III	Min.	0.2	V
$I_H^{(1)}$	$I_T = 500\text{ mA}$		Max.	15	mA
I_L	$I_G = 1.2 I_{GT}$	I - III	Max.	20	mA
		II	Max.	25	mA
$dV/dt^{(1)}$	$V_D = V_R = 536\text{ V}$, gate open	$T_j = 125\text{ °C}$	Min.	250	V/ μ s
	$V_D = V_R = 402\text{ V}$, gate open	$T_j = 150\text{ °C}$		170	V/ μ s
$(dI/dt)_c^{(1)}$	$(dV/dt)_c = 0.1\text{ V}/\mu$ s	$T_j = 125\text{ °C}$	Min.	11.7	A/ms
		$T_j = 150\text{ °C}$		8.2	
$(dI/dt)_c^{(1)}$	$(dV/dt)_c = 10\text{ V}/\mu$ s	$T_j = 125\text{ °C}$	Min.	6	A/ms
		$T_j = 150\text{ °C}$		2.7	

1. For both polarities of A2 referenced to A1

Table 4. Static characteristics

Symbol	Test conditions			Value	Unit
$V_T^{(1)}$	$I_{TM} = 17\text{ A}$, $t_p = 380\ \mu\text{s}$	$T_j = 25\text{ }^\circ\text{C}$	Max.	1.55	V
$V_{i0}^{(1)}$	Threshold voltage	$T_j = 150\text{ }^\circ\text{C}$	Max.	0.85	V
$R_d^{(1)}$	Dynamic resistance	$T_j = 150\text{ }^\circ\text{C}$	Max.	37	m Ω
I_{DRM} I_{RRM}	$V_{DRM} = V_{RRM} = 800\text{ V}$	$T_j = 25\text{ }^\circ\text{C}$	Max.	7.5	μA
		$T_j = 125\text{ }^\circ\text{C}$		1	mA
	$V_{DRM} = V_{RRM} = 600\text{ V}$	$T_j = 150\text{ }^\circ\text{C}$	Max.	2.7	

1. For both polarities of A2 referenced to A1

Table 5. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case (AC)	3.5	$^\circ\text{C/W}$
$R_{th(j-a)}$	Junction to ambient (DC)	60	$^\circ\text{C/W}$

Figure 1. Maximum power dissipation versus on-state rms current (full cycle)

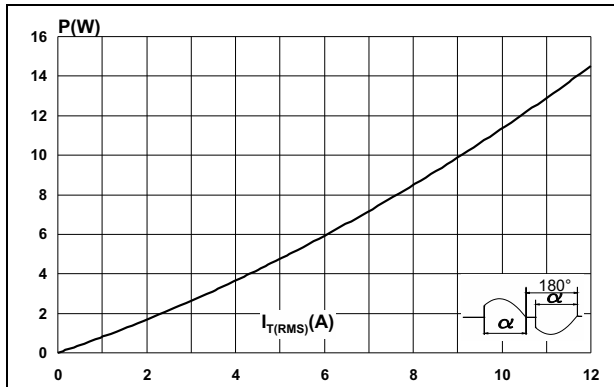


Figure 2. On-state rms current versus case temperature (full cycle)

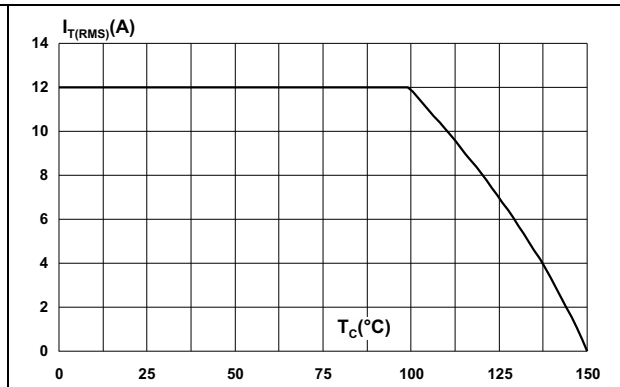


Figure 3. On-state rms current versus ambient temperature (free air convection)

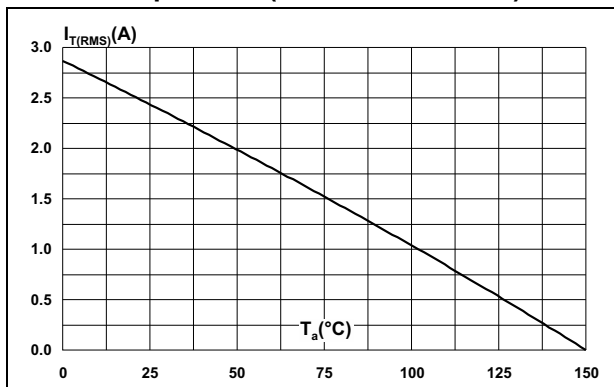


Figure 4. Relative variation of thermal impedance versus pulse duration

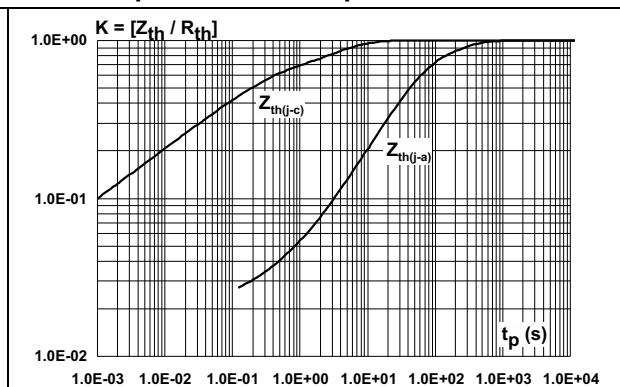


Figure 5. On-state characteristics (maximum values)

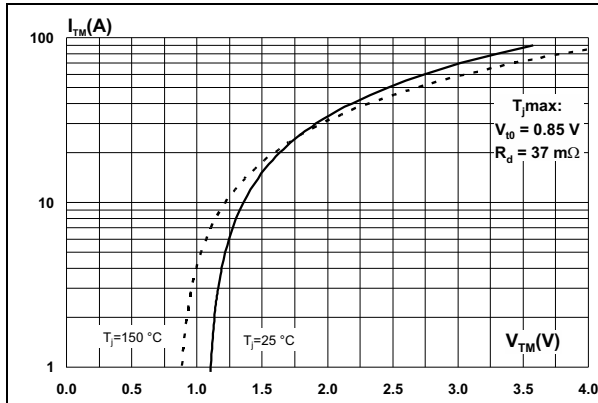


Figure 6. Surge peak on-state current versus number of cycles

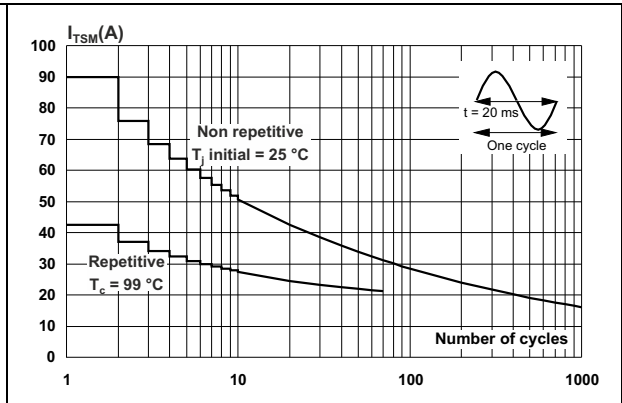


Figure 7. Non repetitive surge peak on-state current and corresponding values of I^2t

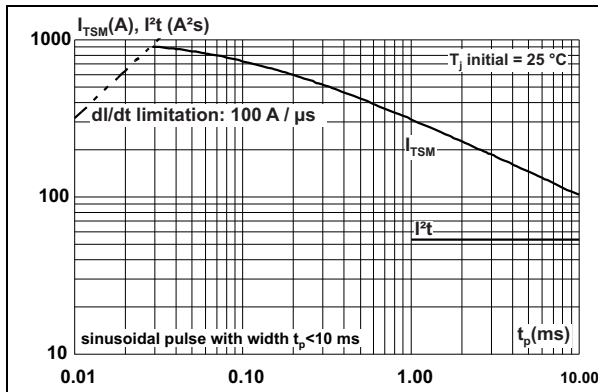


Figure 8. Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)

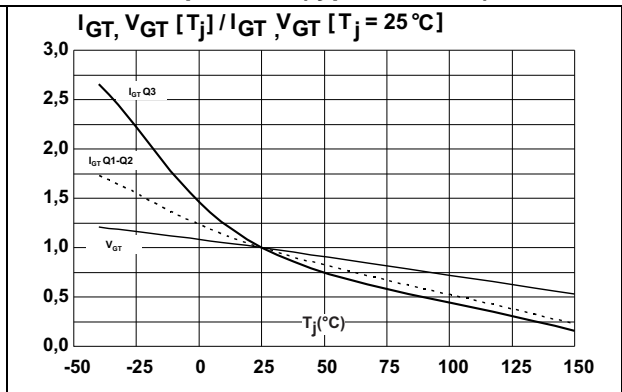


Figure 9. Relative variation of static dV/dt immunity versus junction temperature (typical values)

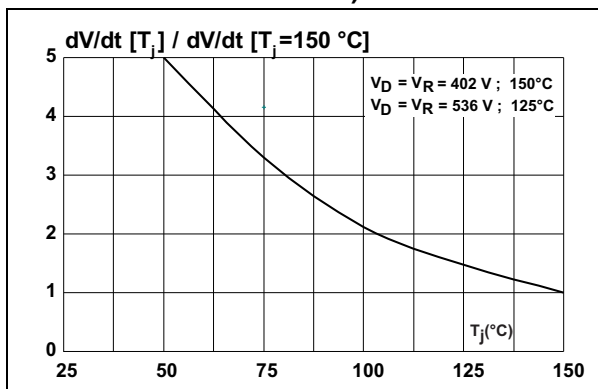


Figure 10. Relative variation of holding and latching current versus junction temperature (typical values)

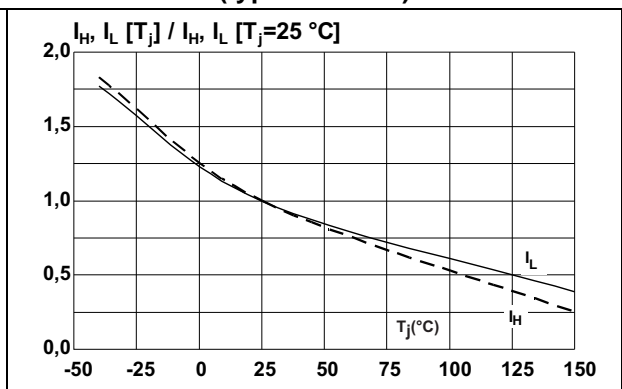


Figure 11. Relative variation of critical rate of decrease of main current (di/dt)_c versus reapplied (dV/dt)_c (typical values)

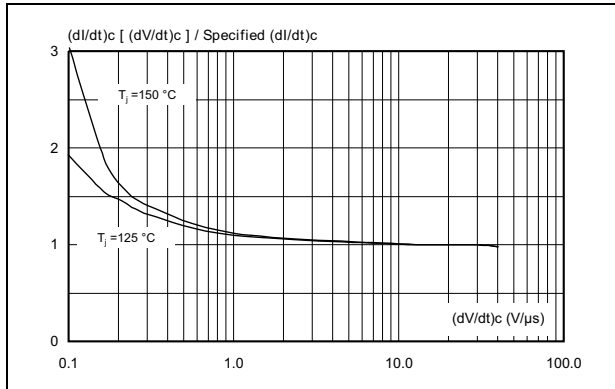


Figure 12. Relative variation of critical rate of decrease of main current (di/dt)_c versus junction temperature (typical values)

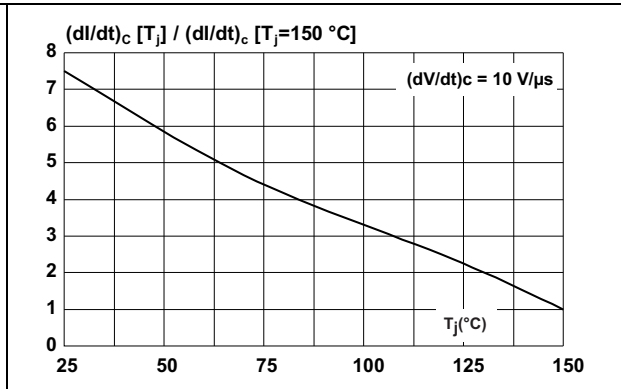
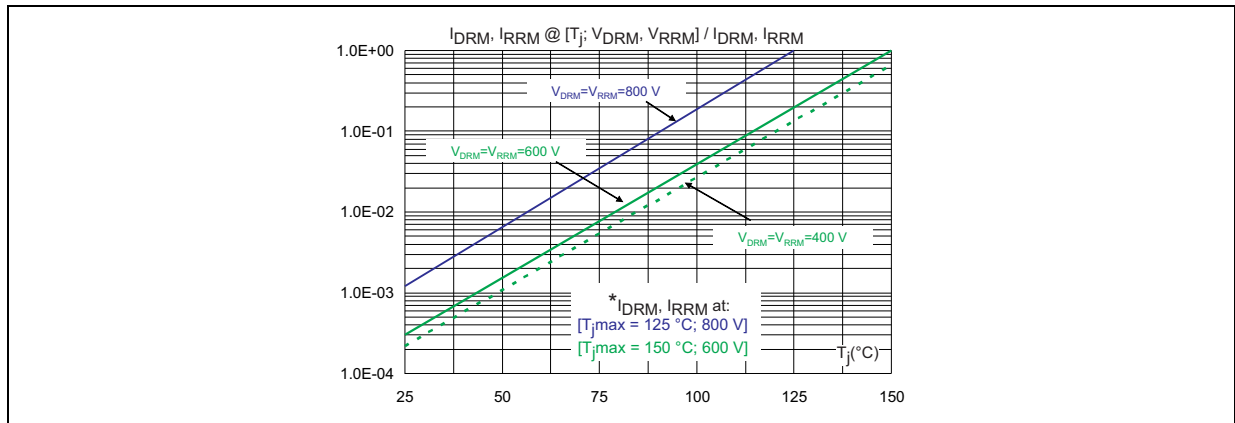


Figure 13. Relative variation of leakage current versus junction temperature for different values of blocking voltage (typical values)



2 Package information

- Epoxy meets UL94, V0
- Lead-free package
- Recommended torque: 0.4 to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 14. TO-220FPAB dimension definitions

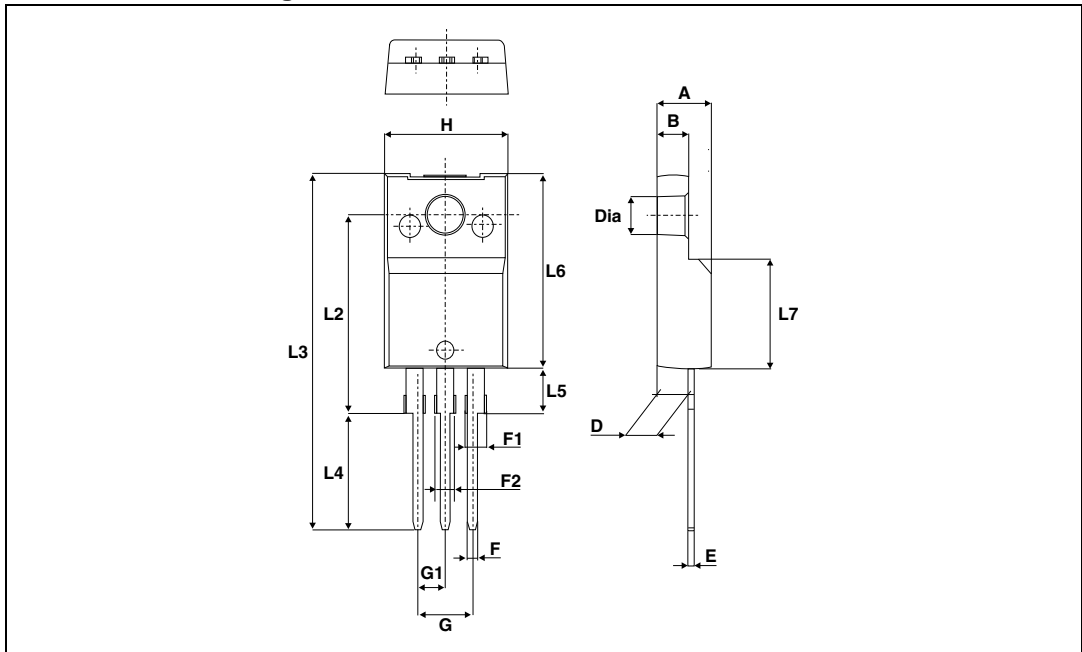


Table 6. TO-220FPAB dimension values

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.4	4.6	0.173	0.181
B	2.5	2.7	0.098	0.106
D	2.5	2.75	0.098	0.108
E	0.45	0.70	0.018	0.027
F	0.75	1	0.030	0.039
F1	1.15	1.70	0.045	0.067
F2	1.15	1.70	0.045	0.067
G	4.95	5.20	0.195	0.205
G1	2.4	2.7	0.094	0.106
H	10	10.4	0.393	0.409
L2	16 Typ.		0.63 Typ.	
L3	28.6	30.6	1.126	1.205
L4	9.8	10.6	0.386	0.417
L5	2.9	3.6	0.114	0.142
L6	15.9	16.4	0.626	0.646
L7	9.00	9.30	0.354	0.366
Dia.	3.00	3.20	0.118	0.126

3 Ordering information

Figure 15. Ordering information scheme

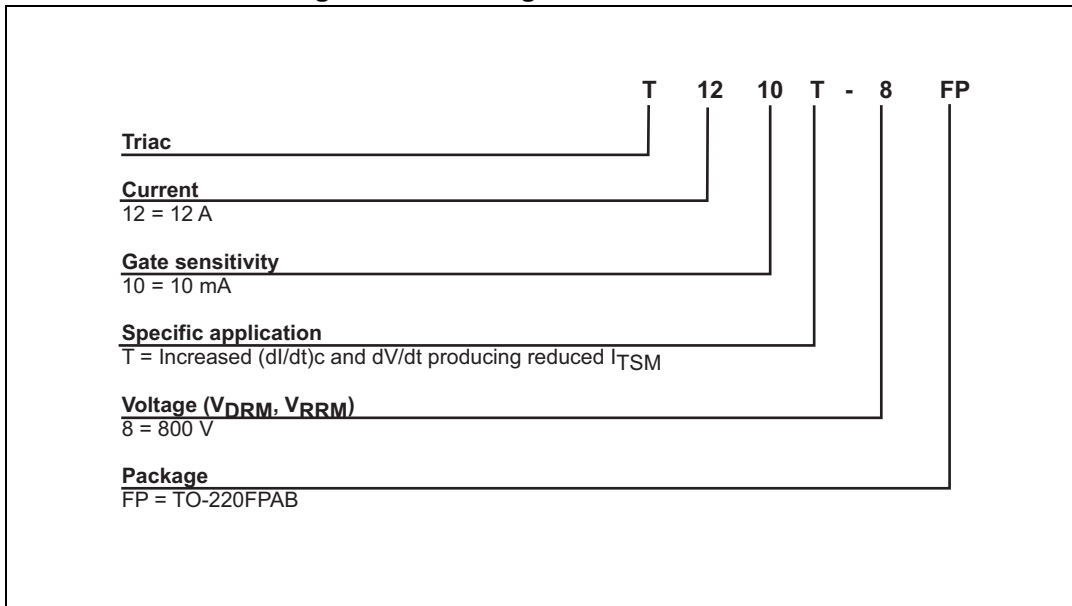


Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T1210T-8FP	T1210T-8FP	TO-220FPAB	2.0 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
31-Jan-2014	1	Initial release.
11-Feb-2015	2	Updated Features and Table 2 .

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2015 STMicroelectronics – All rights reserved

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9